

60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE IntelliFET MOSFET

Product Summary

Continous Drain-Source Voltage: 60V

On-State Resistance: 200mΩ

Nominal Load Current (V_{IN} = 5V): 1.8A

Clamping Energy: 120mJ

Description

The ZXMS6005DN8 is a dual self-protected low-side IntelliFETTM MOSFET with logic level input. It integrates over-temperature, overcurrent, overvoltage (active clamp) and ESD protected logic level functionality. The ZXMS6005DN8 is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

Applications

- Lamp Driver
- Motor Driver
- Relay Driver
- Solenoid Driver

Features and Benefits

- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Overvoltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Overcurrent Protection
- Input Protection (ESD)
- High Continuous Current Rating
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An Automotive-Compliant Part is Available Under Separate Datasheet (ZXMS6005DN8Q)

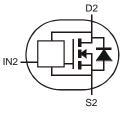
Mechanical Data

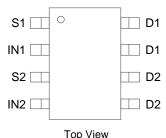
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 79.1mg (Approximate)

SO-8



IN1 IN2 IN2 IN2 Device Symbol





Pin-Out

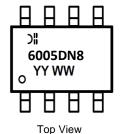
Ordering Information (Note 4)

ĺ	Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
	ZXMS6005DN8-13	6005DN8	13	12	2,500 units

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



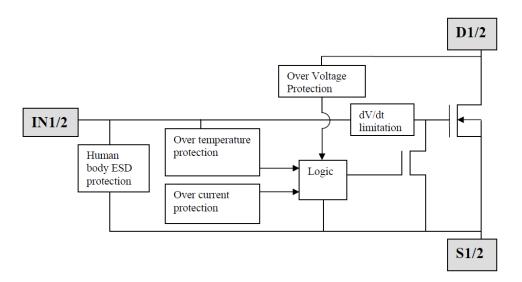
Oll = Manufacturer's Marking 6005DN8 = Product Type Marking Code YYWW = Date Code Marking YY: Year WW: Week: 01~52; 52 represents 52 and 53 week

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ZXMS6005DN8



Functional Block Diagram



Application Information

- Two Completely Isolated Independent Channels
- Especially Suited for Loads with a High In-rush Current Such as Lamps and Motors
- All Types of Resistive, Inductive and Capacitive Loads in Switching Applications
- μC Compatible Power Switch for 12V and 24V DC Applications
- Replaces Electromechanical Relays and Discrete Circuits
- Linear Mode Capability the current-limiting protection circuitry is designed to deactivate at low V_{DS} to minimize on-state power dissipation. The maximum DC operating current is therefore determined by the thermal capability of the package or board combination, rather than by the protection circuitry. This does not compromise the product's ability to self-protect at low V_{DS}

Absolute Maximum Ratings (@TA = +25°C, unless otherwise stated.)

Characteristic	Symbol	Value	Unit
Continuous Drain-Source Voltage	V _{DS}	60	V
Drain-Source Voltage For Short Circuit Protection	V _{DS(SC)}	16	V
Continuous Input Voltage	V _{IN}	-0.5 to +6	V
Continuous Input Current @-0.2V \leq V _{IN} \leq 6V Continuous Input Current @V _{IN} $<$ -0.2V or V _{IN} $>$ 6V	I _{IN}	No limit I _{IN} ≤ 2	mA
Pulsed Drain Current @V _{IN} = 3.3V	I _{DM}	5	Α
Pulsed Drain Current @V _{IN} = 5V	I _{DM}	6	Α
Continuous Source Current (Body Diode) (Note 5)	Is	2.5	Α
Pulsed Source Current (Body Diode)	I _{SM}	10	Α
Unclamped Single Pulse Inductive Energy, T _J = +25°C, I _D = 0.5A, V _{DD} = 24V	E _{AS}	120	mJ
Electrostatic Discharge (Human Body Model)	V_{HBM}	4,000	V
Charged Device Model	V _{CDM}	1,000	V

Note: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Recommended Operating Conditions

The ZXMS6005DN8 is optimized for use with μC operating from 3.3V and 5V supplies.

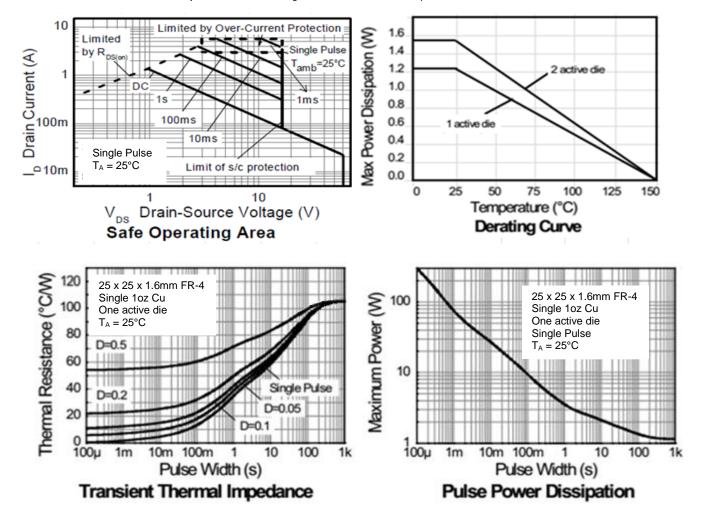
Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	V _{IN}	0	5.5	V
Ambient Temperature Range	T _A	-40	+125	°C
High Level Input Voltage for MOSFET to be On	V _{IH}	3	5.5	V
Low Level Input Voltage for MOSFET to be Off	V _{IL}	0	0.7	V
Peripheral Supply Voltage (Voltage to which load is referred)	V _P	0	16	V

Thermal Characteristics (@TA = +25°C, unless otherwise stated.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = +25°C (Note 5) Linear Derating Factor	P _D	1.21 9.7	W mW/°C
Power Dissipation at T _A = +25°C (Note 6) Linear Derating Factor	P _D	1.56 12.5	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	103	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	81	°C/W
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	13.5	°C/W
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Notes:

^{7.} Thermal resistance between junction and the mounting surfaces of drain and source pins.



^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.



Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Static Characteristics							
Drain-Source Clamp Voltage	V _{DS(AZ)}	60	65	70	V	I _D = 10mA	
Off-State Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 12V, V_{IN} = 0V$	
On-State Diam Current		_	_	2		$V_{DS} = 36V, V_{IN} = 0V$	
Input Threshold Voltage	V _{IN(TH)}	0.7	1	1.5	V	$V_{DS} = V_{GS}$, $I_D = 1mA$	
Input Current		_	60	100	μA	$V_{IN} = 3V$	
Imput Current	I _{IN}	_	120	200		$V_{IN} = 5V$	
Input Current while Over-Temperature Active	_	_	_	300	μA	V _{IN} = 5V	
Static Drain-Source On-State Resistance		_	170	250	mΩ	$V_{IN} = 3V$, $I_D = 1A$	
Static Dialif-Source Off-State Resistance	R _{DS(ON)}	_	150	200		$V_{IN} = 5V, I_D = 1A$	
Continuous Drain Current (Note 5)	- I _D	1.4	_	_		V _{IN} = 3V; T _A = +25°C	
Continuous Diain Curient (Note 5)		1.6	_	_	А	$V_{IN} = 5V$; $T_A = +25$ °C	
Continuous Drain Current (Note 6)		1.7	_	_		$V_{IN} = 3V$; $T_A = +25$ °C	
Continuous Diain Curient (Note 6)		1.8	_	_		$V_{IN} = 5V; T_A = +25^{\circ}C$	
Current Limit (Note 8)	I _{D(LIM)}	2.2	5	_	A	$V_{IN} = 3V$	
Current Limit (Note 8)		3.3	7	_		$V_{IN} = 5V$	
Dynamic Characteristics							
Turn On Delay Time	t _{D(ON)}	_	6	_	μs		
Rise Time	t _R		14	_	μs	$V_{DD} = 12V$, $I_D = 0.5A$, $V_{GS} = 5V$	
Turn Off Delay Time	t _{D(OFF)}	1	34	_	μs	VDD = 12V, ID = 0.5A, VGS = 5V	
Fall Time	t _F		19	_	μs		
Over-Temperature Protection							
Thermal Overload Trip Temperature (Note 9)	T_{JT}	+150	+175	_	°C	_	
Thermal Hysteresis (Note 9)	ΔT_{JT}	_	+10	_	°C	_	

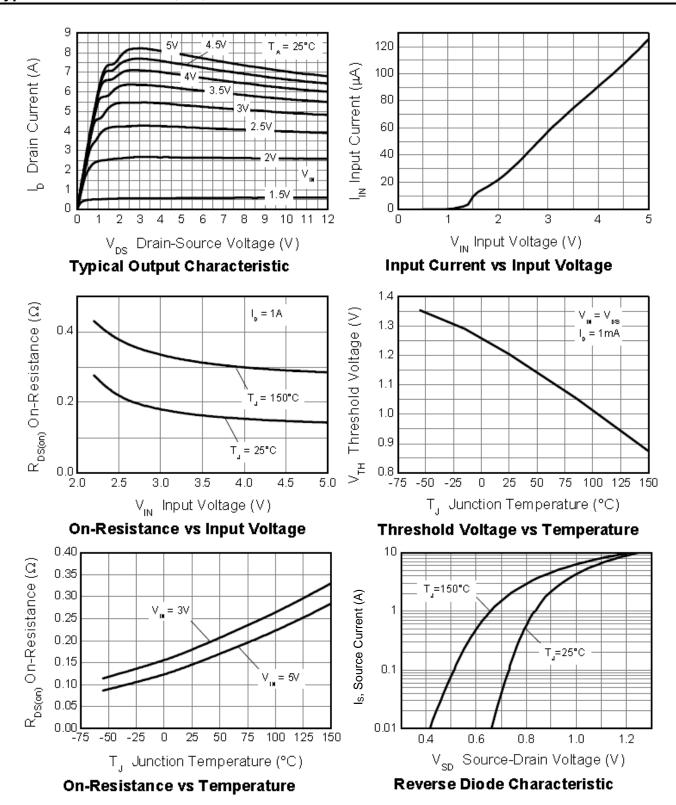
Notes:

^{8.} The drain current is restricted only when the device is in saturation (see graph "Typical Output Characteristic"). This allows the device to be used in the onstate without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.

^{9.} Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods.

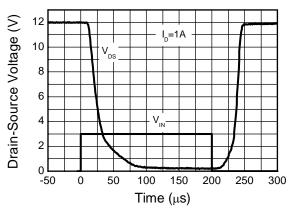


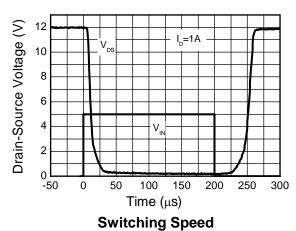
Typical Characteristics (Cont.)



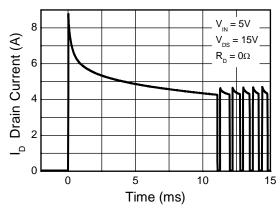


Typical Characteristics (Cont.)





Switching Speed



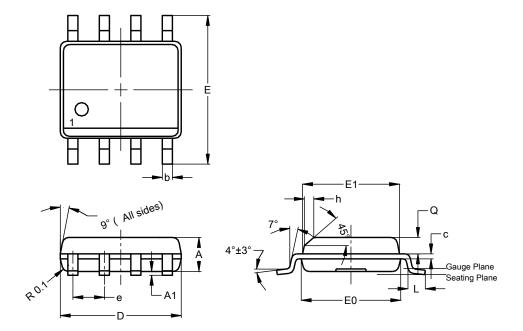
Typical Short Circuit Protection



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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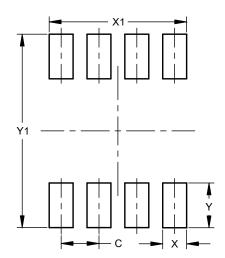


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Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
C	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h	-		0.35		
١	0.62	0.82	0.72		
ø	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

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Dimensions	Value (in mm)		
С	1.27		
Х	0.802		
X1	4.612		
Y	1.505		
Y1	6.50		



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